

learned a lot on the Si technology perspective.

On the same day as the DL, the IRPS 2012 Report Meeting was also held at the university. After a general review of IRPS 2012 by Dr. M. Sato (Toshiba), the following speakers reviewed their IRPS 2012 presentations: Dr. S. Fujii (Toshiba), Dr. C. Yoshida (LEAP), Dr. L. Zhang (Toshiba), Dr. N. Yamaguchiya (Renesas Semiconductor), Dr. H. Nakamura (Renesas Electronics) and Dr. T. Uemura (Fujitsu Semiconductor). Over 30 attendees enjoyed the discussions on the latest device reliability issues and the new analyzing technologies of dopant distributions.



Dr. Tohru Mogami, giving a DL at the University of Tokyo

ED Japan

—by Akira Toriumi

Dr. Tohru Mogami, NEC Corporation, gave a Distinguished Lecture (DL) at The University Tokyo, Tokyo, on July 20, 2012. His lecture on R&D Technology and Production Technology in Advanced Si-CMOS reviewed recent advances of new technology from metal gate/high-k to FinFET technology down to 2x nm generation. He pointed out that Si technology is still ongoing, and new materials and new structures will



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